

FOD817 Series

DESCRIPTION

The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

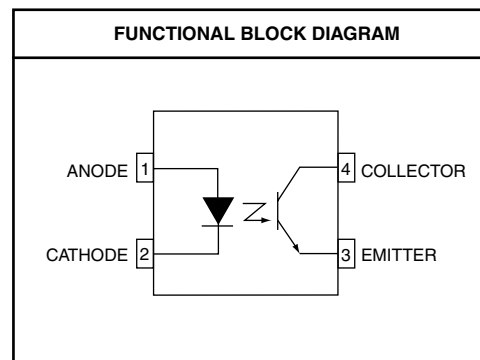
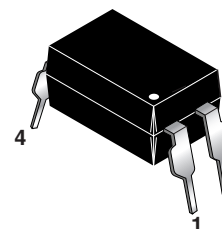
FEATURES

- Applicable to Pb-free IR reflow soldering
- Compact 4-pin package
- Current transfer ratio in selected groups:
 - FOD817: 50-600%
 - FOD817A: 80-160%
 - FOD817B: 130-260%
 - FOD817C: 200-400%
 - FOD817D: 300-600%
- C-UL, UL and VDE approved
- High input-output isolation voltage of 5000 Vrms

APPLICATIONS

FOD817 Series

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless otherwise specified.)			
Parameter	Symbol	Value	Units
TOTAL DEVICE			
Storage Temperature	T _{STG}	-55 to +125	°C
Operating Temperature	T _{OPR}	-30 to +100	°C
Lead Solder Temperature	T _{SOL}	260 for 10 sec	°C
Total Device Power Dissipation	P _D	200	mW
EMITTER			
Continuous Forward Current	I _F	50	mA
Reverse Voltage	V _R	6	V
LED Power Dissipation Derate above 25°C	P _D	70	mW
		0.93	mW/°C
DETECTOR			
Collector-Emitter Voltage	V _{CEO}	70	V
Emitter-Collector Voltage	V _{ECO}	6	V
Continuous Collector Current	I _C	50	mA
Detector Power Dissipation Derate above 25°C	P _D	150	mW
		2.0	mW/°C

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Min	Typ*	Max	Unit
EMITTER						
Input Forward Voltage	($I_F = 20\text{ mA}$)	V_F	—	1.2	1.4	V
Reverse Leakage Current	($V_R = 4.0\text{ V}$)	I_R	—	—	10	μA
Terminal Capacitance	($V = 0, f = 1\text{ kHz}$)	C_t	—	30	250	pF
DETECTOR						
Collector-Emitter Breakdown Voltage	($I_C = 0.1\text{ mA}, I_F = 0$)	BV_{CEO}	70	—	—	V
Emitter-Collector Breakdown Voltage	($I_E = 10\text{ }\mu\text{A}, I_F = 0$)	BV_{ECO}	6	—	—	V
Collector-Emitter Dark Current	($V_{CE} = 20\text{ V}, I_F = 0$)	I_{CEO}	—	—	100	nA

*Typical values at $T_A = 25^\circ\text{C}$.

TRANSFER CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

DC Characteristic	Test Conditions	Symbol	Device	Min	Typ*	Max	Unit
Current Transfer Ratio	($I_F = 5\text{ mA}, V_{CE} = 5\text{ V}$) (note 1)	CTR	FOD817	50	—	600	%
			FOD817A	80	—	160	%
			FOD817B	130	—	260	%
			FOD817C	200	—	400	%
			FOD817D	300	—	600	%
Collector-Emitter Saturation Voltage	($I_F = 20\text{ mA}, I_C = 1\text{ mA}$)	$V_{CE(SAT)}$		—	0.1	0.2	V
AC Characteristic							
Rise Time	($I_C = 2\text{ mA}, V_{CE} = 2\text{ V}, R_L = 100\Omega$) (note 2)	t_r		—	4	18	μs
Fall Time	($I_C = 2\text{ mA}, V_{CE} = 2\text{ V}, R_L = 100\Omega$) (note 2)	t_f		—	3	18	μs

ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ*	Max	Units
Input-Output Isolation Voltage (note 3)	$f = 60\text{ Hz}, t = 1\text{ min}$	V_{ISO}	5000			Vac(rms)
Isolation Resistance	($V_{I-O} = 500\text{ VDC}$)	R_{ISO}	5×10^{10}	10^{11}		Ω
Isolation Capacitance	($V_{I-O} = 0, f = 1\text{ MHz}$)	C_{ISO}		0.6	1.0	pf

*Typical values at $T_A = 25^\circ\text{C}$.

NOTES

- Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- For test circuit setup and waveforms, refer to page 4.
- For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

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Typical Electrical/Optical Characteristic Curves ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

Fig. 1 Forward Current vs. Ambient Temperature

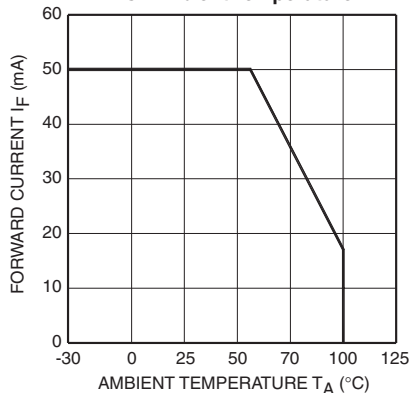


Fig. 2 Collector Power Dissipation vs. Ambient Temperature

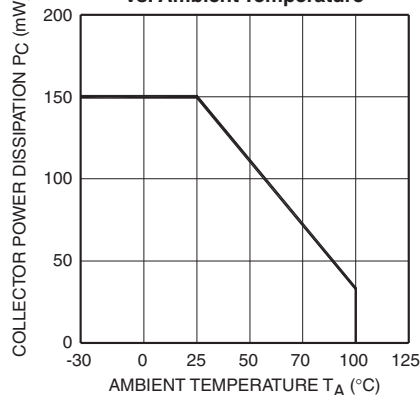


Fig. 3 Collector-Emitter Saturation Voltage vs. Forward Current

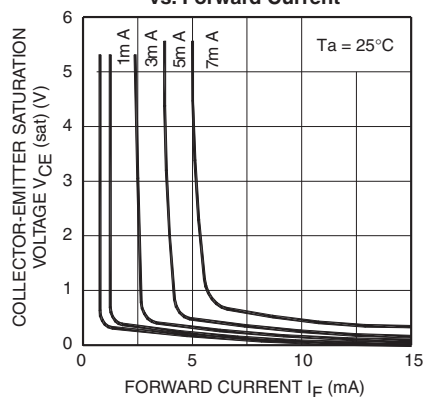


Fig. 4 Forward Current vs. Forward Voltage

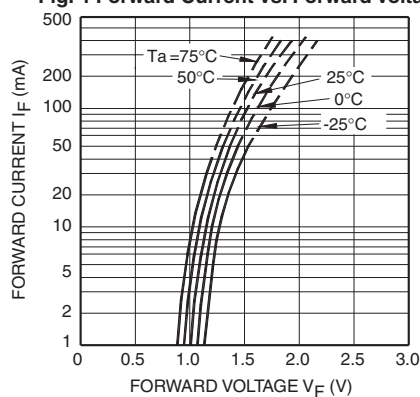


Fig. 5 Current Transfer Ratio vs. Forward Current

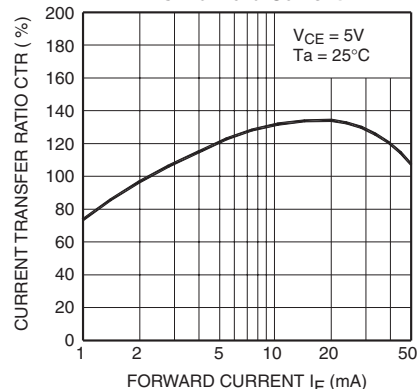
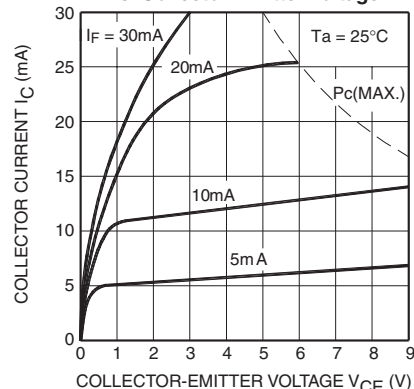


Fig. 6 Collector Current vs. Collector-Emitter Voltage



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Typical Electrical/Optical Characteristic Curves ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

Fig. 7. Relative Current Transfer Ratio vs. Ambient Temperature

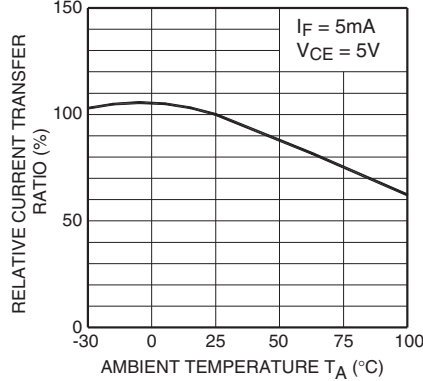


Fig. 8 Collector-Emitter Saturation Voltage vs. Ambient Temperature

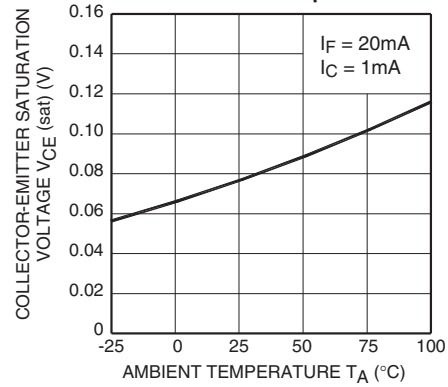


Fig. 9 Collector Dark Current vs. Ambient Temperature

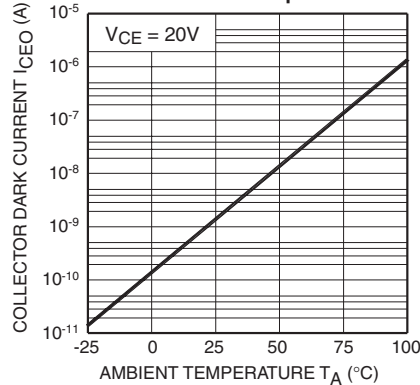


Fig. 10. Response Time vs. Load Resistance

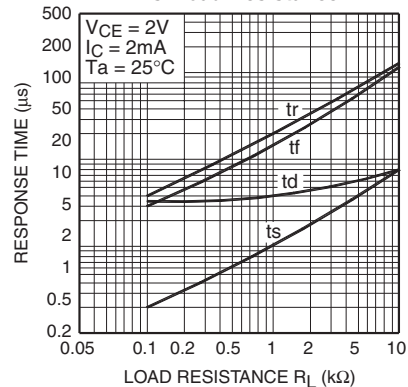
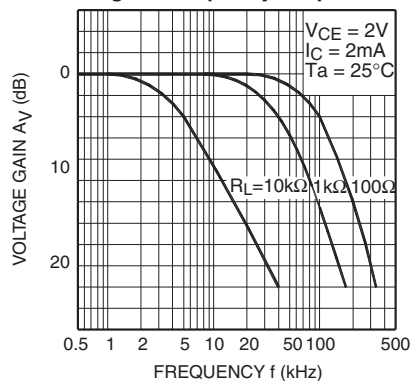
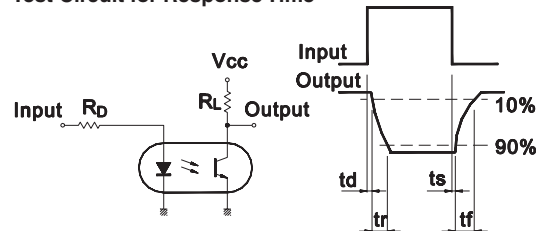


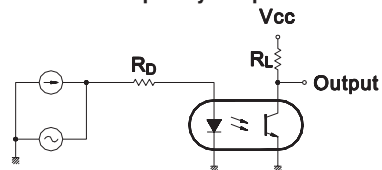
Fig. 11. Frequency Response



Test Circuit for Response Time

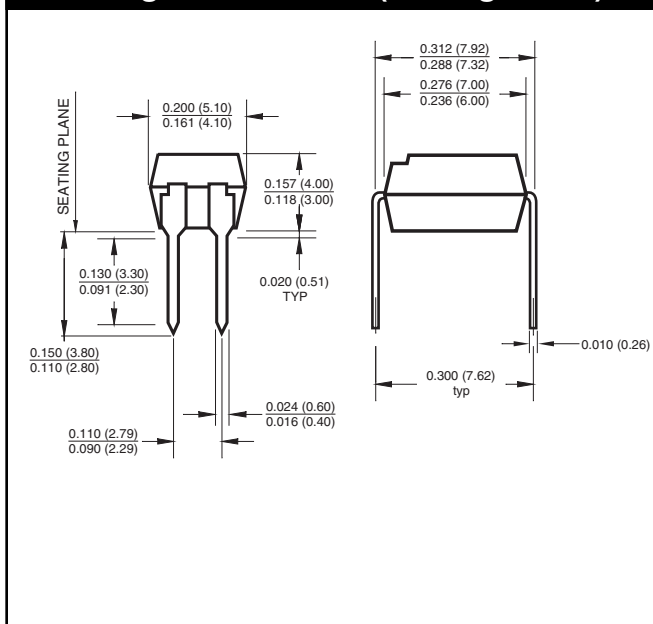


Test Circuit for Frequency Response

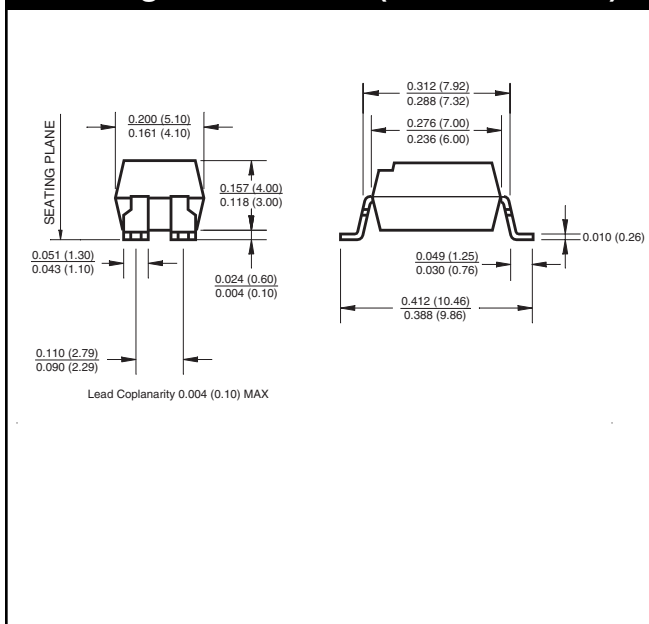


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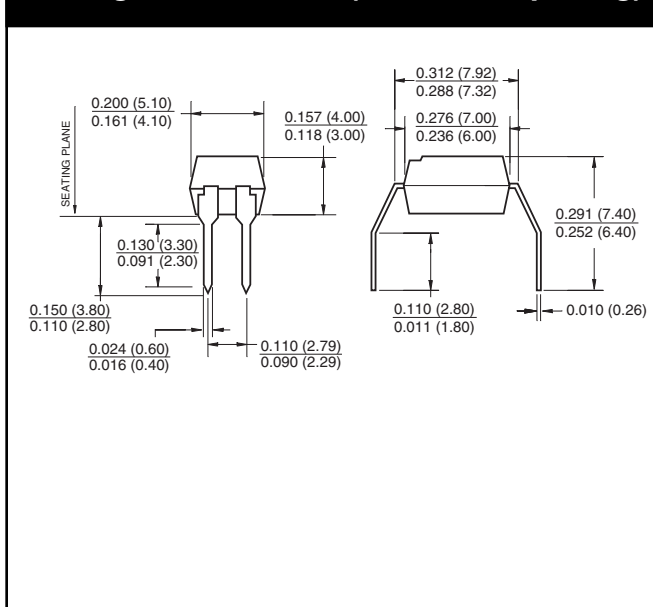
Package Dimensions (Through Hole)



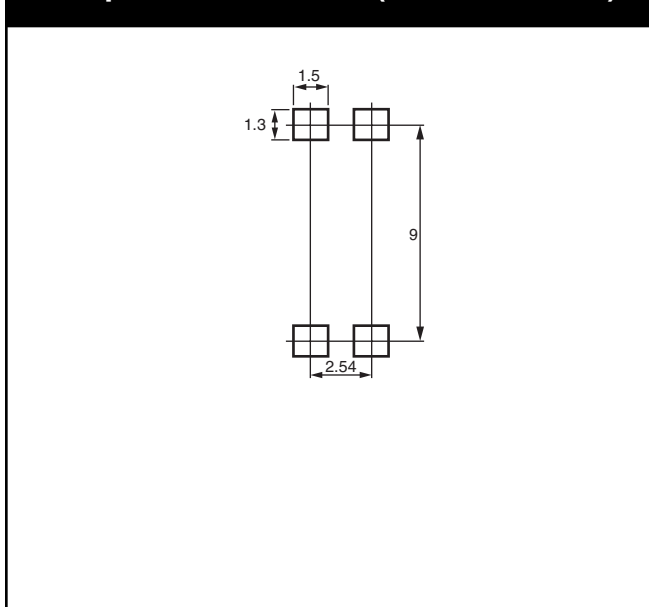
Package Dimensions (Surface Mount)



Package Dimensions (0.4" Lead Spacing)



Footprint Dimensions (Surface Mount)



NOTE

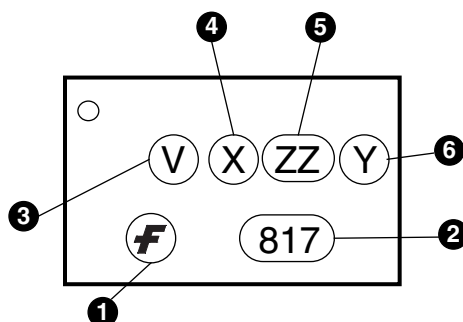
All dimensions are in inches (millimeters)

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ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel

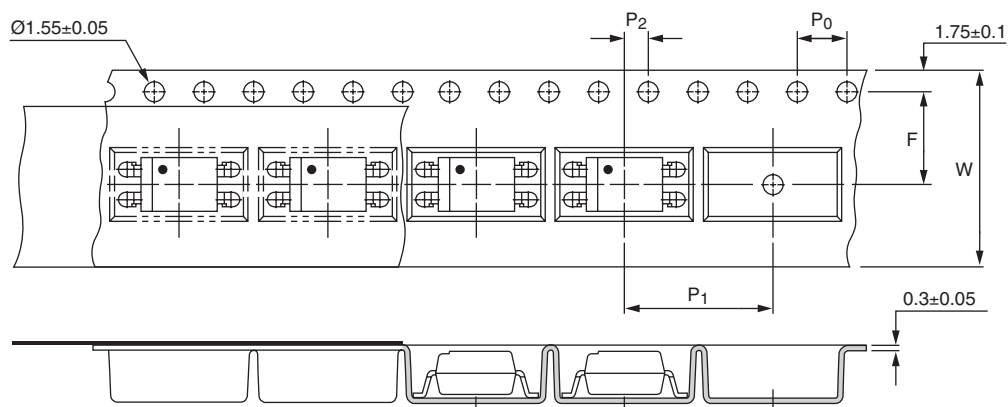
MARKING INFORMATION



Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

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Carrier Tape Specifications



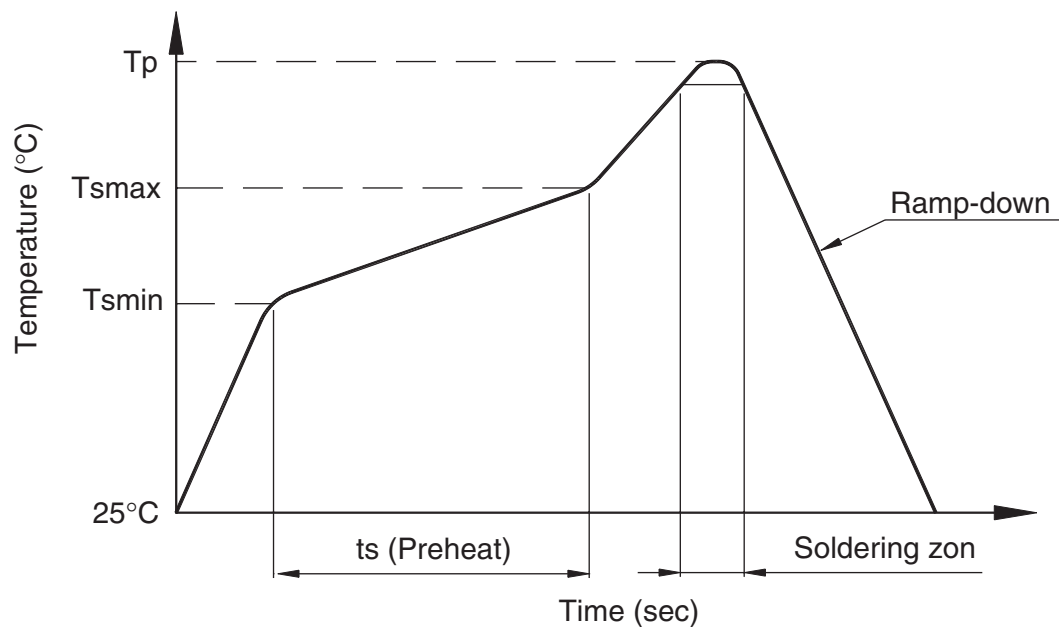
NOTE

All dimensions are in millimeters

Description	Symbol	Dimensions in mm (inches)
Tape wide	W	16 ± 0.3 (.63)
Pitch of sprocket holes	P ₀	4 ± 0.1 (.15)
Distance of compartment	F P ₂	7.5 ± 0.1 (.295) 2 ± 0.1 (.079)
Distance of compartment to compartment	P ₁	12 ± 0.1 (.472)

FOD817 Series

Lead Free recommended IR Reflow condition



Profile Feature	Pb-Sn solder assembly	Lead Free assembly
Preheat condition (Tsmmin-Tsmmax / ts)	100°C ~ 150°C 60 ~ 120 sec	150°C ~ 200°C 60 ~ 120 sec
Melt soldering zone	183°C 60 ~ 120 sec	217°C 30 ~ 90 sec
Peak temperature (Tp)	240 +0/-5°C	250 +0/-5°C
Ramp-down rate	6°C/sec max.	6°C/sec max.

Recommended Wave Soldering condition

Profile Feature	For all solder assembly
Peak temperature (Tp)	Max 260°C for 10 sec

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